

Part Number

Customer

Category	Parameter	Specification	Measurement Method	
OverallWafer	1.0	Diameter	100.00 +/- 0.50 mm	
	2.0	Primary Flat Orientation	{110} +/- 1.0 degree	Wafer Vendor
	3.0	Primary Flat Length	32.50 +/- 2.50 mm	Wafer vendor
	4.0	Notch or Flat	Flat	Wafer Vendor
	5.0	Secondary Flat Orientation	None	Wafer Vendor
	6.0	Overall Thickness	482.00 +/- 12.00 µm	ADE, 100%
	7.0	Total Thickness Variation (TTV)	<5.00µm	Guaranteed by Process
	8.0	Bow	<80.00µm	ADE to ASTM F534, 100%
	9.0	Warp	<80.00µm	
	10.0	Edge Chips	0	Bright Light, 100% (note 2)
	11.0	Edge Exclusion	5mm	
HandleSilicon	12.0	Handle Growth Method	CZ	Wafer Vendor
	13.0	Handle Orientation	{100} +/- 1.0 degree	Wafer Vendor
	14.0	Handle Thickness	380.00 +/- 10.00 µm	ADE, 100%
	15.0	Handle Doping Type	P	Wafer Vendor
	16.0	Handle Dopant	Boron	Wafer Vendor
	17.0	Handle Resistivity	1 ~ 10 Ohmcm	Wafer Vendor
	18.0	Backside Finish	Polished with Oxide and lasermark	Wafer Vendor
	BuriedOxide	19.0	Oxide Type	Thermal
20.0		Oxide Thickness	20,000.00 +/- 1,000.00 A	Nanospec centre point, 4%
DeviceSilicon	21.0	Device Growth Method	CZ	Wafer Vendor
	22.0	Device Orientation	{100} +/- 1.0 degree	Wafer Vendor
	23.0	Nominal Thickness	100.00 +/- 1.00 µm	Filmetrics, 9 point, 100%
	24.0	Distance to device silicon edge from wafer edge	<= 2mm	Typical by Process
	25.0	Device Doping Type	P	Wafer Vendor
	26.0	Device Dopant	Boron	Wafer Vendor
	27.0	Device Resistivity	0.01 ~ 0.02 Ohmcm	Wafer Vendor
	28.0	Voids	none	Bright Light, 100% (note 2)
	29.0	Scratches	0	Bright Light, 100% (note 2)
	30.0	Haze	none	Bright Light, 100% (note 2)
	31.0	LPD Count	<30 >0.3um	Guaranteed by process

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Shipping Details	Wafer per box :	Max 25	
	Packaging :	Taped Polypropylene Wafer Box Empak, Ultrapak, 100.00mm Antistatic Double Bagging	
	Lot Shipment Data	Device Thickness Bow / Warp Data Handle and SOI Thickness	



Explanatory Notes 1. Microscope inspection performed using microscope scan as below. 5x objective.

2. All bright light inspections performed exclude all wafer area outside the edge exclusion defined in Overall Wafer, Edge Exclusion. High intensity bright lamp inspection as per ASTM F523.

3. 9 point measurement are as shown in the diagram below:



Additional Information